

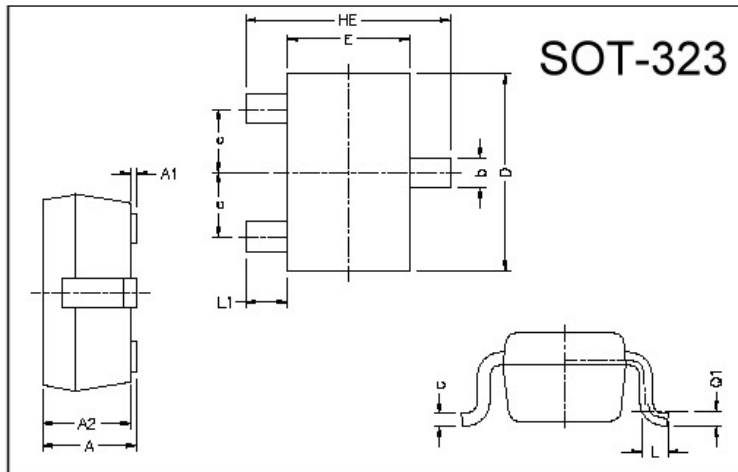
GSD2656

NPN EPITAXIAL TRANSISTOR

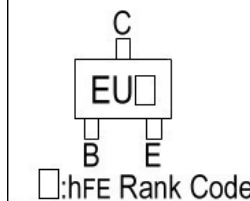
Description

The GSD2656 is designed for general purpose amplifier applications.

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	VCBO	30	V
Collector to Emitter Voltage	VCEO	30	V
Emitter to Base Voltage	VEBO	6	V
Collector Current	IC	1	A
Total Power Dissipation	PD	225	mW

Electrical Characteristics (Ta = 25°C, unless otherwise noted)

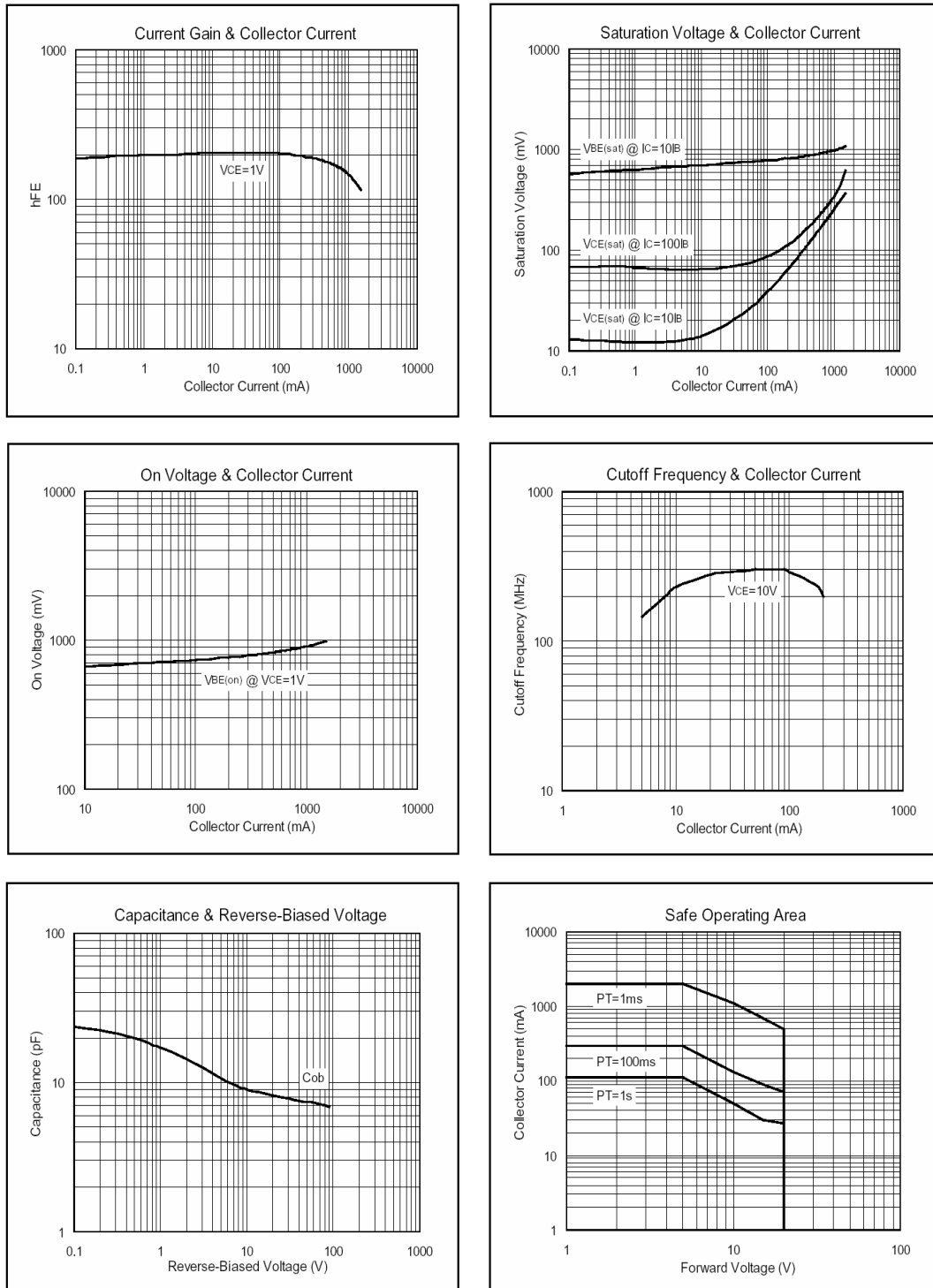
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	30	-	-	V	IC=10uA, IE=0
BVCEO	30	-	-	V	IC=1mA, IB=0
BVEBO	6	-	-	V	IE=10uA, IC=0
ICBO	-	-	100	nA	VCB=30V, IE=0
IEBO	-	-	100	nA	VEB=6V, IC=0
VCE(sat)	-	-	350	mV	IC=500mA, IB=25mA
*hFE	120	-	500		VCE=2V, IC=100mA
*fT	-	400	-	MHz	VCE=2V, IE=-100mA, f=100MHz
Cob	-	5	-	pF	VCB=10V, f=1MHz

*Pulsed Test

Classification Of hFE

Rank	EUC	EUD	EUE
Range	120 ~ 200	160 ~ 300	250 ~ 500

Characteristics Curve



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